STMicroelectronics - STM32F334R8T6TR Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 21x12b; D/A 3x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f334r8t6tr

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3.5 Interconnect matrix

Several peripherals have direct connections between them. This allows autonomous communication between peripherals, saving CPU resources thus power supply consumption. In addition, these hardware connections allow fast and predictable latency.

Table 4. STM32F334x4/6/8 peripheral interconnect matrix

Interconnect source	Interconnect destination	Interconnect action
TIMx	TIMx	Timers synchronization or chaining
	ADCx DACx	Conversion triggers
	DMA	Memory to memory transfer trigger
	COMPx	Comparator output blanking
COMPx	TIMx	Timer input: ocrefclear input, input capture
ADCx	TIM/HRTIM1	Timer triggered by analog watchdog
GPIO RTCCLK HSE/32 MC0	TIM16	Clock source used as input channel for HSI and LSI calibration
CSS CPU (hard fault) RAM (parity error) COMPx PVD GPIO	TIM1 TIM15, 16, 17	Timer break
GPIO	TIMx	External trigger, timer break
	ADCx DACx	Conversion external trigger
DACx	COMPx	Comparator inverting input
HRTIM1	DACx/ADCx	Conversion trigger
COMPx	HRTIM1	COMPx output is an input event or a fault input for HRTIM1
OPAMP2	HRTIM1	OPAMP2 output is an input event for HRTIM1
GPIO	HRTIM1	External fault/event/ Synchro inputs for HRTIM1
HRTIM1	GPIO	Synchro output for HRTIM1

Note: For more details about the interconnect actions, refer to the corresponding sections in the RM0364 reference manual.

3.14.1 217 ps high-resolution timer (HRTIM1)

The high-resolution timer (HRTIM1) allows generating digital signals with high-accuracy timings, such as PWM or phase-shifted pulses.

It consists of 6 timers, 1 master and 5 slaves, totaling 10 high-resolution outputs, which can be coupled by pairs for deadtime insertion. It also features 5 fault inputs for protection purposes and 10 inputs to handle external events such as current limitation, zero voltage or zero current switching.

HRTIM1 timer is made of a digital kernel clocked at 144 MHz followed by delay lines. Delay lines with closed loop control guarantee a 217 ps resolution whatever the voltage, temperature or chip-to-chip manufacturing process deviation. The high-resolution is available on the 10 outputs in all operating modes: variable duty cycle, variable frequency, and constant ON time.

The slave timers can be combined to control multiswitch complex converters or operate independently to manage multiple independent converters.

The waveforms are defined by a combination of user-defined timings and external events such as analog or digital feedbacks signals.

HRTIM1 timer includes options for blanking and filtering out spurious events or faults. It also offers specific modes and features to offload the CPU: DMA requests, burst mode controller, push-pull and resonant mode.

It supports many topologies including LLC, Full bridge phase shifted, buck or boost converters, either in voltage or current mode, as well as lighting application (fluorescent or LED). It can also be used as a general purpose timer, for instance to achieve high-resolution PWM-emulated DAC.

In debug mode, the HRTIM1 counters can be frozen and the PWM outputs enter safe state.

3.14.2 Advanced timer (TIM1)

The advanced-control timer can be seen as a three-phase PWM multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers. The 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIM timers (described in *Section 3.14.3* using the same architecture, so the advanced-control timers can work together with the TIM timers via the Timer Link feature for synchronization or event chaining.

3.14.7 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

3.15 Real-time clock (RTC) and backup registers

The RTC and the 5 backup registers are supplied through a switch that takes power from either the V_{DD} supply when present or the VBAT pin. The backup registers are five 32-bit registers used to store 20 bytes of user application data when V_{DD} power is not present.

They are not reset by a system or power reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms with wake up from Stop and Standby mode capability.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy.
- Two anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.
- 17-bit Auto-reload counter for periodic interrupt with wakeup from STOP/STANDBY capability.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 40 kHz)
- The high-speed external clock divided by 32.

Table 13. STM32F334x4/6/8 pin definitions (continued)

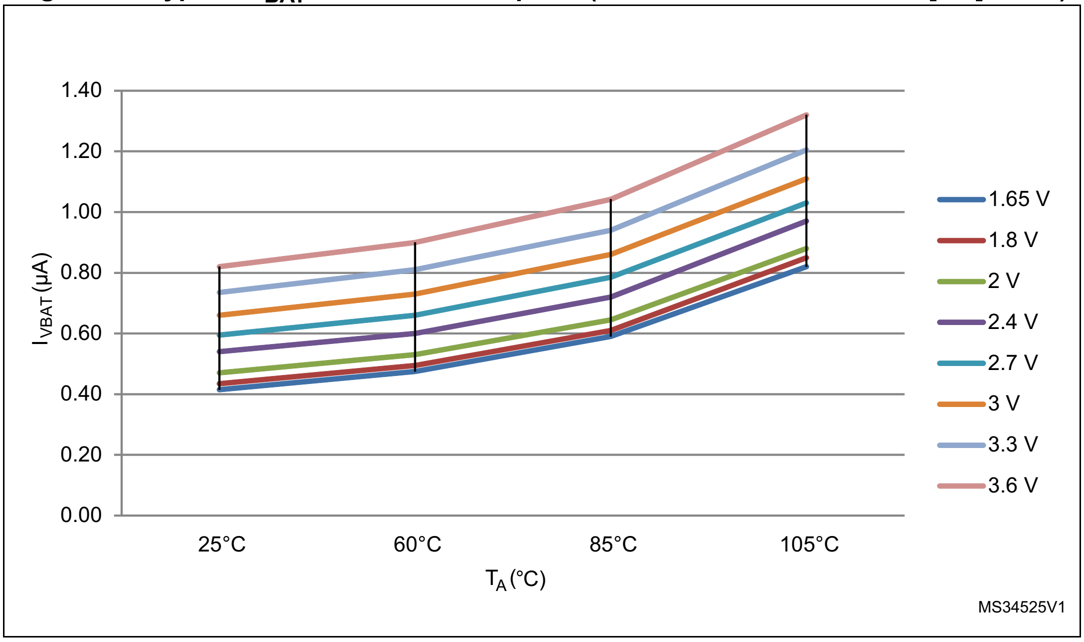
Pin Number			Pin name (function after reset)	Pin type	I/O structure	Pin functions	
LQFP 32	LQFP 48	LQFP 64				Alternate functions	Additional functions
23	34	46	PA13	I/O	FT	JTMS/SWDAT, TIM16_CH1N, TSC_G4_IO3, IR_OUT, USART3_CTS, EVENTOUT	-
-	35	47	VSS	S	-	-	-
-	36	48	VDD	S	-	-	-
24	37	49	PA14	I/O	FTf	JTCK/SWCLK, TSC_G4_IO4, I2C1_SDA, TIM1_BKIN, USART2_TX, EVENTOUT	-
25	38	50	PA15	I/O	FTf	JTDI, TIM2_CH1/TIM2_ETR, TSC_SYNC, I2C1_SCL, SPI1_NSS, USART2_RX, TIM1_BKIN, HRTIM1_FLT2, EVENTOUT	-
-	-	51	PC10	I/O	FT	EVENTOUT, USART3_TX	-
-	-	52	PC11	I/O	FT	EVENTOUT, HRTIM1_EEV2, USART3_RX	-
-	-	53	PC12	I/O	FT	EVENTOUT, HRTIM1_EEV1, USART3_CK	-
-	-	54	PD2	I/O	FT	EVENTOUT, TIM3_ETR	-
26	39	55	PB3	I/O	FT	JTDO/TRACE SWO, TIM2_CH2, TSC_G5_IO1, SPI1_SCK, USART2_TX, TIM3_ETR, HRTIM1_SCOUT, HRTIM1_EEV9, EVENTOUT	-
27	40	56	PB4	I/O	FT	NJTRST, TIM16_CH1, TIM3_CH1, TSC_G5_IO2, SPI1_MISO, USART2_RX, TIM17_BKIN, HRTIM1_EEV7, EVENTOUT	-

Table 13. STM32F334x4/6/8 pin definitions (continued)

Pin Number			Pin name (function after reset)	Pin type	I/O structure	Pin functions	
LQFP 32	LQFP 48	LQFP 64				Alternate functions	Additional functions
28	41	57	PB5	I/O	FT	TIM16_BKIN, TIM3_CH2, I2C1_SMBA, SPI1_MOSI, USART2_CK, TIM17_CH1, HRTIM1_EEV6, EVENTOUT	-
29	42	58	PB6	I/O	FTf	TIM16_CH1N, TSC_G5_IO3, I2C1_SCL, USART1_TX, HRTIM1_SCIN, HRTIM1_EEV4, EVENTOUT	-
30	43	59	PB7	I/O	FTf	TIM17_CH1N, TSC_G5_IO4, I2C1_SDA, USART1_RX, TIM3_CH4, HRTIM1_EEV3, EVENTOUT	-
31	44	60	BOOT0	I	B	-	-
-	45	61	PB8	I/O	FTf	TIM16_CH1, TSC_SYNC, I2C1_SCL, USART3_RX, CAN_RX, TIM1_BKIN, HRTIM1_EEV8, EVENTOUT	-
-	46	62	PB9	I/O	FTf	TIM17_CH1, I2C1_SDA, IR_OUT, USART3_TX, COMP2_OUT, CAN_TX, HRTIM1_EEV5, EVENTOUT	-
32	47	63	VSS	S	-	-	-
1	48	64	VDD	S	-	-	-

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch sinks only a limited amount of current (3 mA), the use of GPIO PC13 to PC15 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF
   - These GPIOs must not be used as current sources (e.g. to drive an LED).
   After the first backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the Backup registers which is not reset by the main reset. For details on how to manage these GPIOs, refer to the Battery backup domain and BKP register description sections in the reference manual.
2. Fast ADC channel.
3. These GPIOs offer a reduced touch sensing sensitivity. It is thus recommended to use them as sampling capacitor I/O.

Figure 12. Typical V_{BAT} current consumption (LSE and RTC ON/LSEDRV[1:0] = ’00’)



Typical current consumption

The MCU is placed under the following conditions:

- $V_{DD} = V_{DDA} = 3.3$ V
- All I/O pins available on each package are in analog input configuration
- The Flash access time is adjusted to f_{HCLK} frequency (0 wait states from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states from 48 MHz to 72 MHz), and Flash prefetch is ON
- When the peripherals are enabled, $f_{APB1} = f_{AHB/2}$, $f_{APB2} = f_{AHB}$
- PLL is used for frequencies greater than 8 MHz
- AHB prescaler of 2, 4, 8,16 and 64 is used for the frequencies 4 MHz, 2 MHz, 1 MHz, 500 kHz and 125 kHz respectively.

Table 30. Typical current consumption in Run mode, code with data processing running from Flash memory

Symbol	Parameter	Conditions	f_{HCLK}	Typ.		Unit
				Peripherals enabled	Peripherals disabled	
I_{DD}	Supply current in Run mode from V_{DD} supply	Running from HSE crystal clock 8 MHz, code executing from Flash	72 MHz	70.6	25.2	mA
			64 MHz	60.3	22.6	
			48 MHz	46.0	17.3	
			32 MHz	31.3	12.0	
			24 MHz	25.0	9.3	
			16 MHz	16.2	6.5	
			8 MHz	8.4	3.55	
			4 MHz	4.75	2.21	
			2 MHz	2.81	1.52	
			1 MHz	1.82	1.17	
			500 kHz	1.34	0.94	
			125 kHz	0.93	0.82	
I_{DDA} (1) (2)	Supply current in Run mode from V_{DDA} supply		72 MHz	240.0	234.0	µA
			64 MHz	209.9	208.6	
			48 MHz	154.5	153.5	
			32 MHz	104.1	103.6	
			24 MHz	80.2	80.0	
			16 MHz	56.8	56.6	
			8 MHz	1.14	1.14	
			4 MHz	1.14	1.14	
			2 MHz	1.14	1.14	
			1 MHz	1.14	1.14	
			500 kHz	1.14	1.14	
			125 kHz	1.14	1.14	

1. V_{DDA} supervisor is OFF.
2. When peripherals are enabled, the power consumption of the analog part of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.

Table 39. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)

Symbol	Parameter	Conditions(1)	Min. (2)	Typ.	Max.(2)	Unit
I_{DD}	LSE current consumption	LSEDRV[1:0]=00 lower driving capability	-	0.5	0.9	µA
		LSEDRV[1:0]=10 medium low driving capability	-	-	1	
		LSEDRV[1:0]=01 medium high driving capability	-	-	1.3	
		LSEDRV[1:0]=11 higher driving capability	-	-	1.6	
g_m	Oscillator transconductance	LSEDRV[1:0]=00 lower driving capability	5	-	-	µA/V
		LSEDRV[1:0]=10 medium low driving capability	8	-	-	
		LSEDRV[1:0]=01 medium high driving capability	15	-	-	
		LSEDRV[1:0]=11 higher driving capability	25	-	-	
$t_{SU(LSE)}$(3)	Startup time	V_{DD} is stabilized	-	2	-	s

1. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
2. Guaranteed by design, not tested in production.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 43. Flash memory characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.(1)	Unit
t_{prog}	16-bit programming time	T_A = –40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (2 KB) erase time	T_A = –40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = –40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

Table 44. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value Min.(1)	Unit
N_{END}	Endurance	TA = –40 to +85 °C (6 suffix versions) TA = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycles(2) at T_A = 55 °C	20	

1. Data based on characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 45*. They are based on the EMS levels and classes defined in application note AN1709.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset occurrence or oscillator frequency deviation). The test results are given in *Table 49: I/O current injection susceptibility*.

Table 49. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	– 0	NA	mA
	Injected current on PC0, PC1, PC2, PC3 (TTa pins) and PF1 pin (FT pin)	-0	+5	
	Injected current on PA0, PA1, PA2, PA3, PA4, PA5, PA6, PA7, PC4, PC5, PB0, PB1, PB2, PB12, PB13, PB14, PB15 with induced leakage current on other pins from this group less than -100 µA or more than +900 µA	-5	+5	
	Injected current on PB11, other TT, FT, and FTf pins	– 5	NA	
	Injected current on all other TC, TTa and RESET pins	– 5	+5	

Note: It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 19*. All I/Os are CMOS and TTL compliant.

Table 50. I/O static characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{IL}	Low level input voltage	TT, TC and TTa I/O	-	-	$0.3\ V_{DD}+0.07$ (1)	V
		FT and FTf I/O	-	-	$0.475\ V_{DD}-0.2$ (1)	
		BOOT0	-	-	$0.3\ V_{DD}-0.3$ (1)	
		All I/Os except BOOT0	-	-	$0.3\ V_{DD}$ (2)	
V_{IH}	High level input voltage	TTa and TT I/O	$0.445\ V_{DD}+0.398$ (1)	-	-	
		FT and FTf I/O	$0.5\ V_{DD+0.2}$ (1)	-	-	
		BOOT0	$0.2\ V_{DD}+0.95$ (1)	-	-	
		All I/Os except BOOT0	$0.7\ V_{DD}$ (2)	-	-	

Table 55. HRTIM output response to fault protection[1]

Symbol	Parameter	Conditions	Min	Typ.	Max.[2]	Unit
$t_{LAT(DF)}$	Digital fault response latency	Propagation delay from HRTIM1_FLTx digital input to HRTIM_CHxy output pin	-	12	25	ns
$t_{W(FLT)}$	Minimum Fault pulse width	-	12.5	-	-	
$t_{LAT(AF)}$	Analog fault response latency	Propagation delay from comparator COMPx_INP input pin to HRTIM_CHxy output pin	-	25	43	

1. Refer to Fault paragraph in HRTIM section of RM0364.
2. Data based on characterization results, not tested in production.

Table 56. HRTIM output response to external events 1 to 5 (Low-Latency mode[1])

Symbol	Parameter	Conditions	Min	Typ.	Max.[2]	Unit
$t_{LAT(DEEV)}$	Digital external event response latency	Propagation delay from HRTIM1_EEVx digital input to HRTIM_CHxy output pin (30pF load)	-	12	25	ns
$t_{W(FLT)}$	Minimum external event pulse width	-	12.5	-	-	ns
$t_{LAT(AEEV)}$	Analog external event response latency	Propagation delay from comparator COMPx_INP input pin to HRTIM_CHxy output pin (30pF load)	-	25	43	ns
$T_{JIT(EEV)}$	External event response jitter	Jitter of the delay from HRTIM1_EEVx digital input or COMPx_INP input pin to HRTIM_CHxy output pin	-	-	0	t_{HRTIM}[3]
$T_{JIT(PW)}$	Jitter on output pulse width in response to an external event	-	-	-	1	t_{HRTIM}[3]

1. EExFAST bit in HRTIM_EECR1 register is set (Low Latency mode). This functionality is available on external events channels 1 to 5. Refer to Latency to external events paragraph in HRTIM section of RM0364.
2. Data based on characterization results, not tested in production.
3. $T_{HRTIM} = 1 / f_{HRTIM}$ with f_{HRTIM}= 144 MHz or f_{HRTIM} = 128 MHZ depending on the clock controller configuration. (Refer to Reset and clock control section in RM0364.)

6.3.17 Timer characteristics

The parameters given in *Table 59* are guaranteed by design.

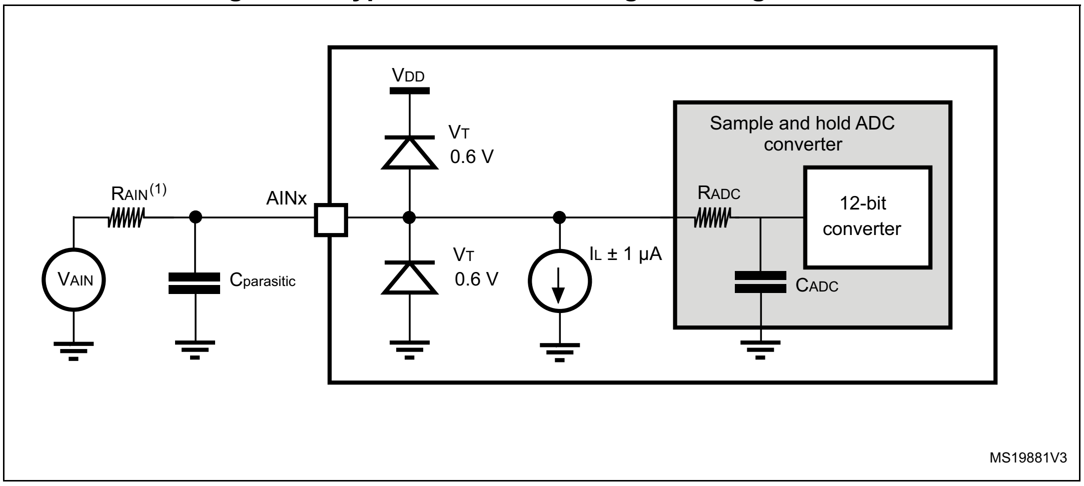
Refer to *Section 6.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 59. TIMx(1)(2) characteristics

Symbol	Parameter	Conditions	Min.	Max.	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	13.9	-	ns
		$f_{TIM1CLK}$ = 144 MHz	6.95	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 72 MHz	0	36	MHz
Res_{TIM}	Timer resolution	TIMx (except TIM2)	-	16	bit
		TIM2	-	32	
$t_{COUNTER}$	16-bit counter clock period	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	0.0139	910	µs
		$f_{TIM1CLK}$ = 144 MHz	0.0069	455	µs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 72 MHz	-	59.65	s
		$f_{TIM1CLK}$ = 144 MHz	-	29.825	s

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM3,TIM15, TIM16 and TIM17 timers.
2. Guaranteed by design, not tested in production.

Figure 29. Typical connection diagram using the ADC



1. Refer to *Table 64* for the values of R_{AIN}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 10: Power-supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.20 DAC electrical specifications

Table 69. DAC characteristics

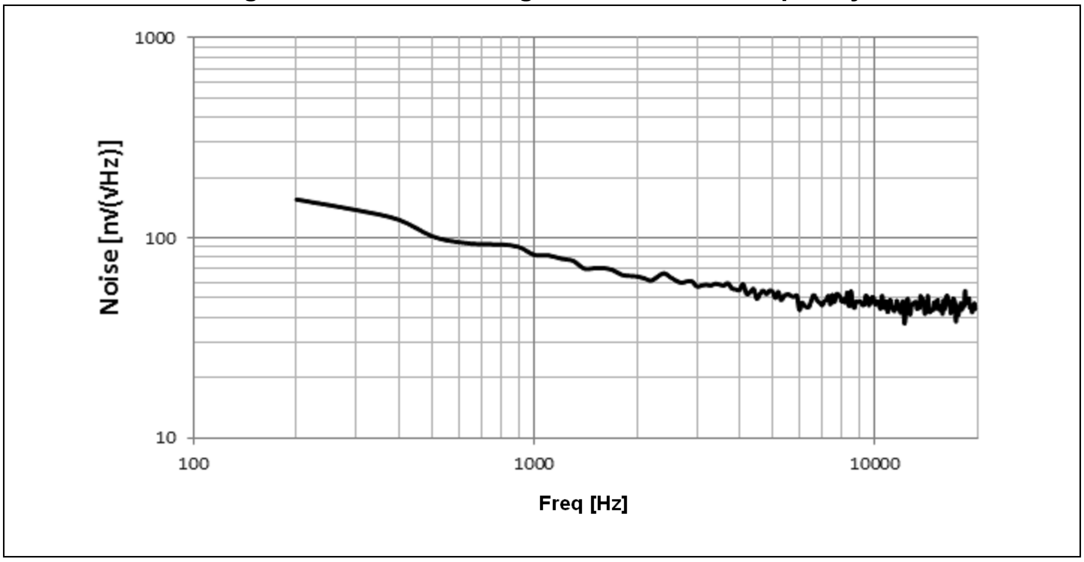
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{DDA}	Analog supply voltage	-	2.4	-	3.6	V
R_{LOAD}(1)	Resistive load	DAC output buffer ON (to V_{SSA})	5	-	-	kΩ
R_{LOAD}(1)	Resistive load	DAC output buffer ON (to V_{DDA})	25	-	-	kΩ
R_O(1)	Output impedance	DAC output buffer OFF	-	-	15	kΩ
C_{LOAD}(1)	Capacitive load	DAC output buffer ON	-	-	50	pF
V_{DAC_OUT}(1)	Voltage on DAC_OUT output	Corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{DDA} = 3.6 V and (0x155) and (0xEAB) at V_{DDA} = 2.4 V	0.2	-	$V_{DDA} – 0.2$	V
		DAC output buffer OFF	-	0.5	-	mV
			-	-	V_{DDA}– 1LSB	V
I_{DDA}(3)	DAC DC current consumption in quiescent mode(2)	With no load, middle code (0x800) on the input	-	-	380	µA
		With no load, worst code (0xF1C) on the input.	-	-	480	µA

Table 71. Operational amplifier characteristics[1] (continued)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
en	Voltage noise density	@ 1KHz, Output loaded with 4 KΩ	-	109	-	$\frac{nV}{\sqrt{Hz}}$
		@ 10KHz, Output loaded with 4 KΩ	-	43	-	

1. Guaranteed by design, not tested in production.
2. The saturation voltage can also be limited by the I_{load}.
3. R2 is the internal resistance between OPAMP output and OPAMP inverting input. R1 is the internal resistance between OPAMP inverting input and ground. The PGA gain =1+R2/R1
4. Mostly TTa I/O leakage, when used in analog mode.

Figure 32. OPAMP Voltage Noise versus Frequency



6.3.23 Temperature sensor (TS) characteristics

Table 72. Temperature sensor (TS) characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{25}	Voltage at 25 °C	1.34	1.43	1.52	V
t_{START}(1)	Startup time	4	-	10	µs
T_{S_temp}(1)(2)	ADC sampling time when reading the temperature	2.2	-	-	µs

1. Guaranteed by design, not tested in production.
2. Shortest sampling time can be determined in the application by multiple iterations.

Table 73. Temperature sensor (TS) calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3.3 V	0x1FFF F7B8 - 0x1FFF F7B9
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C V_{DDA}= 3.3 V	0x1FFF F7C2 - 0x1FFF F7C3

6.3.24 V_{BAT} monitoring characteristics

Table 74. V_{BAT} monitoring characteristics

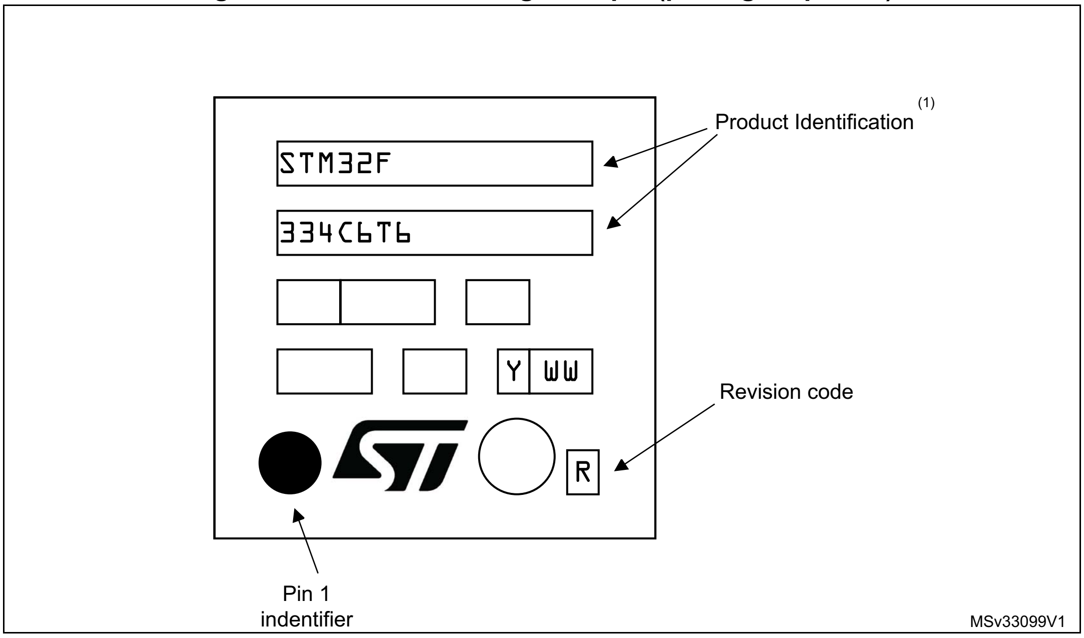
Symbol	Parameter	Min.	Typ.	Max.	Unit
R	Resistor bridge for V_{BAT}	-	50	-	KΩ
Q	Ratio on V_{BAT} measurement	-	2	-	-
Er(1)	Error on Q	-1	-	+1	%
T_{S_vbat}(1)(2)	ADC sampling time when reading the V_{BAT} 1mV accuracy	2.2	-	-	µs

1. Guaranteed by design, not tested in production.
2. Shortest sampling time can be determined in the application by multiple iterations.

Device marking for LQFP48

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 38. LQFP48 marking example (package top view)

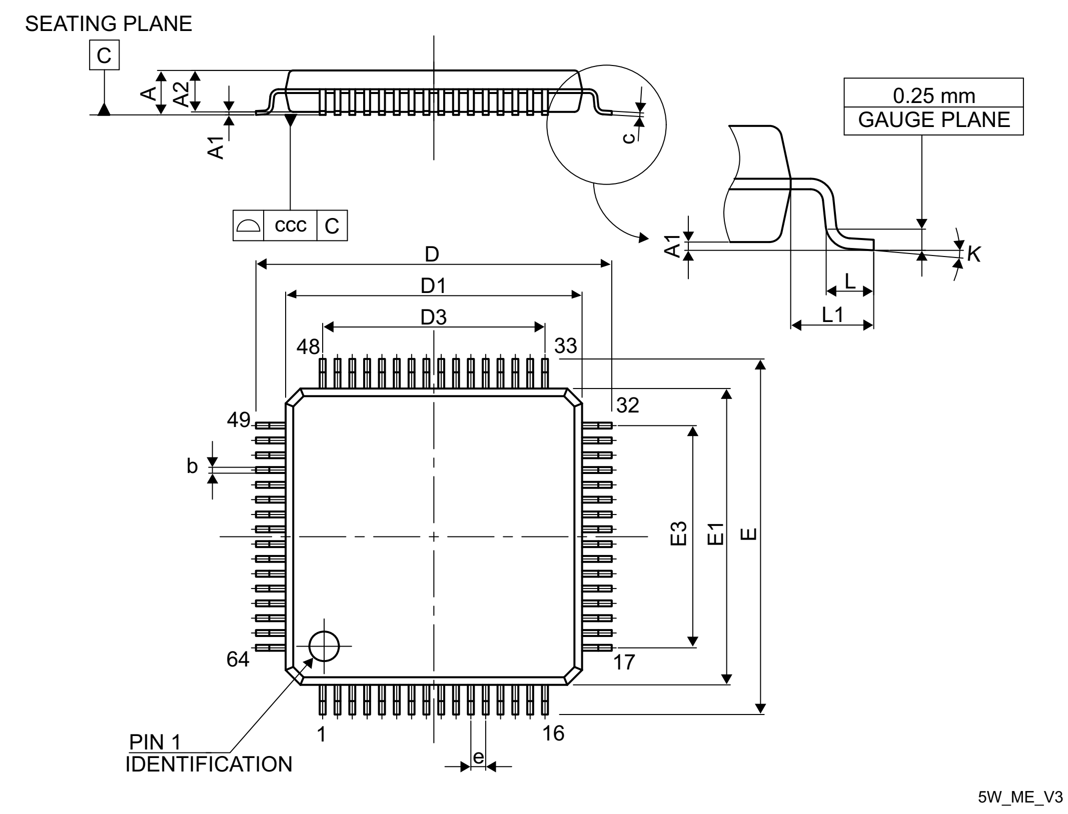


1. Parts marked as “ES”,”E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.4 LQFP64 package information

LQFP64 is a 64-pin, 10 x 10 mm low-profile quad flat package.

Figure 39. LQFP64 package outline



1. Drawing is not to scale.

Table 77. LQFP64 package mechanical data

Symbol	millimeters			inches[(1)]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	11.800	12.000	-	-	0.4724	-
D1	9.800	10.000	-	-	0.3937	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
e	-	0.500	-	-	0.0197	-

8 Part numbering

Table 79. Ordering information scheme

Example:	STM32	F	334	C	8	T	6	xxx

Device family

STM32 = ARM®-based 32-bit microcontroller

Product type

F = general-purpose

Device subfamily

334 = STM32F334xx, 2.0 to 3.6 V operating voltage

Pin count

K = 32 pins

C = 48 pins

R = 64 pins

Flash memory size

4 = 16 Kbytes of Flash memory

6 = 32 Kbytes of Flash memory

8 = 64 Kbytes of Flash memory

Package

T = LQFP

Temperature range

6 = Industrial temperature range, –40 to 85 °C

7 = Industrial temperature range, –40 to 105 °C

Options

xxx = programmed parts

TR = tape and reel